

WHAT IS CLAIMED IS:

1. A semiconductor laser device comprising:
a first-conductivity type substrate;
5 a first-conductivity type clad layer formed over the substrate;
an active layer formed over the first-conductivity type clad layer;
a second-conductivity type clad layer formed over the
10 active layer while having a ridge spaced apart, at respective opposite longitudinal ends thereof, from a laser emitting end surface and an end surface opposite to the laser emitting end surface by a predetermined gap; and
a current blocking layer formed on the second-
15 conductivity type clad layer around the ridge.

2. The semiconductor laser device according to claim 1, wherein the predetermined gap is 5 μm or more while corresponding to 10% or less of a distance between the laser
20 emitting end surface and the opposite end surface.

3. A method for manufacturing a semiconductor laser device, comprising the steps of:
sequentially forming over at least a first-
25 conductivity type clad layer, an active layer and a second-

conductivity type clad layer over a substrate;

forming, on the second-conductivity type clad layer,
a mask adapted to form a ridge such that the ridge is spaced
apart, at respective opposite longitudinal ends thereof, from a
5 laser emitting end surface and an end surface opposite to the
laser emitting end surface by a predetermined gap;

etching the second-conductivity type clad layer to a
predetermined depth by use of the mask, thereby forming the
ridge; and

10 forming a current blocking layer made of a first-
conductivity type semiconductor material on the etched second-
conductivity type clad layer around the ridge.

4. The method according to claim 3, wherein the
15 predetermined gap is 5 μm or more while corresponding to 10% or
less of a distance between the laser emitting end surface and
the opposite end surface.

5. The method according to claim 3, wherein the step of
20 forming the ridge comprises the steps of:

forming a ridge structure in accordance with a dry
etching process; and

removing defects formed on a surface of the ridge
structure in accordance with a wet etching process, thereby
25 forming the ridge.